

F1 cont
power source wire 200 from the input/output terminal 212 through the circuit elements, a potential difference ΔV is generated between both terminals of the MOS capacitor 206. If the potential difference ΔV exceeds the electrostatic breakdown voltage, the MOS capacitor 206 is subjected to the electrostatic breakdown.

Please delete the paragraph bridging pages 17 and 18, and replace it with the following new paragraph:

F2
An electrostatic protection element (CDM protection element) 18 is provided between the ground terminal 14 and the MOS capacitor 16 in parallel to the MOS capacitor 16. This electrostatic protection element 18 has a function of clamping the voltage generated between both terminals of the MOS capacitor 16 at the time of the CDM test be a voltage lower than the dielectric breakdown voltage. This electrostatic protection element 18 is, for example, a MOS field effect transistor, the drain of which is connected to the power source wire 10 and the source and gate of which are connected to the ground potential wire 12. It is noted that the electrostatic protection element is not limited to a field effect transistor, but a bipolar transistor, a thyristor or a diode (excluding a parasitic diode) may be used as the electrostatic protection element 18.

Page 28, please delete the second full paragraph, and replace it with the following new paragraph:

F3
Furthermore, as shown in Fig. 9, a bipolar transistor is constituted by closely forming N^+ diffusion layers 74 and 76 so as to face each other. This bipolar transistor constitutes electrostatic